

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF5175** is Designed for High Power Class C Amplifier in, 225 to 400 MHz Military Communication Equipment.

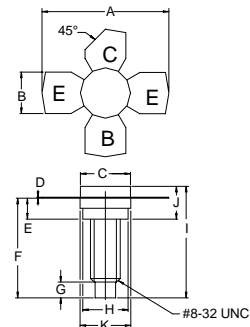
FEATURES:

- Class C Operation
- $P_G = 11$ dB at 5.0 W/400 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	1.0 A
V_{CB}	60 V
V_{CE}	33 V
P_{DISS}	12 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	12°C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 30$ mA	33			V
BV_{CES}	$I_C = 30$ mA	60			V
BV_{EBO}	$I_E = 1.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			0.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 250$ mA	10		100	---
C_{ob}	$V_{CB} = 30$ V $f = 1.0$ MHz			15	pF
P_G	$V_{CC} = 28$ V $P_{OUT} = 5.0$ W $f = 400$ MHz	11			dB
η_D		50			%